

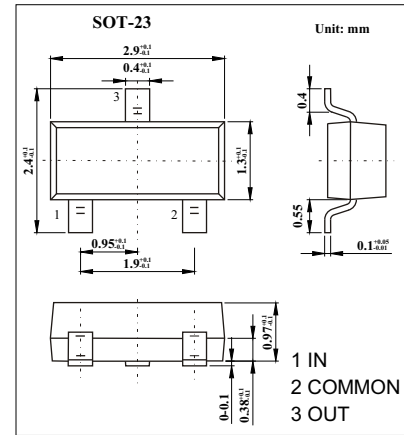
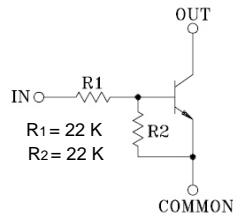
Epitaxial Planar NPN Transistor KRC103S

Features

With Built-in Bias Resistors.

Simplify Circuit Design.

Reduce a Quantity of Parts and Manufacturing Process.



Absolute Maximum Ratings Ta = 25

Parameter	Symbol	Rating	Unit
Output Voltage	V _O	50	V
Input Voltage	V _I	40,-10	V
Output Current	I _O	100	mA
Power Dissipation	P _D	200	mW
Junction Temperature	T _j	150	
Storage Temperature Range	T _{stg}	50	

Electrical Characteristics Ta = 25

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Output Cut-off Current	I _{O(OFF)}	V _O =50V, V _I =0			500	nA
DC Current Gain	G _I	V _O =5V, I _O =10mA	70	120		
Output Voltage	V _{O(ON)}	I _O =10mA, I _I =0.5mA		0.1	0.3	V
Input Voltage (ON)	V _{I(ON)}	V _O =0.2V, I _O =5mA		2.1	3.0	V
Input Voltage (OFF)	V _{I(OFF)}	V _O =5V, I _O =0.1mA	1.0	1.2		V
Input Current	I _I	V _I =5V			0.36	mA
Switching Rise Time	t _r	V _O =5V, V _{IN} =5V, R _L =1k		0.12		μs
Switching Storage Time	t _{stg}			2.0		
Switching Fall Time	t _f			0.35		
Input Resistance	R _I			22		K
Transition Frequency	f _T *	V _O =10V, I _O =5mA		200		MHz

* Characteristic of Transistor Only.

Marking

Marking	NC

KRC103S

■ Typical Characteristics

